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Vishay Siliconix

# Automotive P-Channel 60 V (D-S) MOSFET



Marking Code: 9D

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	-60			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.290			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.395			
I <sub>D</sub> (A)	-1.6			
Configuration	Single			
Package	SC-70			

#### **FEATURES**

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R<sub>q</sub> and UIS tested
- Typical ESD protection: 800 V
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>





ROHS COMPLIANT HALOGEN FREE

	(1, 2, 5, 6) D
(3) G <b>O</b> —	
P-Channel MOSFET	(4) S

<b>ABSOLUTE MAXIMUM RATING</b>	<b>S</b> ( $T_C = 25  ^{\circ}C$ , unles	s otherwise noted	d)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		$V_{DS}$	-60	V
Gate-source voltage		$V_{GS}$	± 20	ľ
Continuous drain current	T <sub>C</sub> = 25 °C a		-1.6	
	T <sub>C</sub> = 125 °C		-1	
Continuous source current (diode conduction	I <sub>S</sub>	-1.6	А	
ulsed drain current <sup>b</sup>		I <sub>DM</sub>		-6.7
Single pulse avalanche current	L = 0.1 mH	I <sub>AS</sub>	-8	
Single pulse avalanche energy	L = U.1 IIIII	E <sub>AS</sub>	3.2	mJ
Maximum power dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	P <sub>D</sub>	2.7	W
	T <sub>C</sub> = 125 °C		0.5	
Operating junction and storage temperature	range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-ambient P	CB mount c	$R_{thJA}$	125	°C/W		
Junction-to-foot (drain)		R <sub>thJF</sub>	45	C/VV		

#### Notes

- a. Package limited
- b. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %
- c. When mounted on 1" square PCB (FR4 material)



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PARAMETER	SYMBOL	TES	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-source breakdown voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$		-60	-	-	V
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	V <sub>GS</sub> , I <sub>D</sub> = -250 μA	-1.5	-2.0	-2.5	V
Gate-source leakage		V <sub>DS</sub> =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$		-	± 5	μΑ
	I <sub>GSS</sub>	V <sub>DS</sub> =	$0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$	-	-	± 5	mA
		$V_{GS} = 0 V$	$V_{DS} = -60 \text{ V}$	-	-	-1	
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = -60 V, T <sub>J</sub> = 125 °C	-	-	-50	μA
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = -60 V, T <sub>J</sub> = 150 °C	-	-	-150	
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = -10 V	$V_{DS} \le -5 V$	-5	-	-	Α
		V <sub>GS</sub> = -10 V	I <sub>D</sub> = -2 A	-	0.230	0.290	
Drain-source on-state resistance <sup>a</sup>	Ь	V <sub>GS</sub> = -10 V	I <sub>D</sub> = -2 A, T <sub>J</sub> = 125 °C	-	-	0.470	Ω
Drain-source on-state resistance "	R <sub>DS(on)</sub>	V <sub>GS</sub> = -10 V	I <sub>D</sub> = -2 A, T <sub>J</sub> = 150 °C	-	-	0.566	
		V <sub>GS</sub> = -4.5 V	I <sub>D</sub> = -1 A	-	0.305	0.395	
Forward transconductance b	9 <sub>fs</sub>	V <sub>DS</sub> =	-10 V, I <sub>D</sub> = -1.5 A	-	3	-	S
Dynamic <sup>b</sup>							
Input capacitance	C <sub>iss</sub>			-	284	355	
Output capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>GS</sub> = 0 V V <sub>DS</sub> = -25 V, f = 1 MHz		36	45	рF
Reverse transfer capacitance	C <sub>rss</sub>			-	28	35	1
Total gate charge <sup>c</sup>	Qg			-	3.6	5.4	
Gate-source charge <sup>c</sup>	Q <sub>gs</sub>	$V_{GS} = -4.5 \text{ V}$	$V_{DS} = -30 \text{ V}, I_{D} = -1 \text{ A}$	-	1.2	-	nC
Gate-drain charge <sup>c</sup>	$Q_{gd}$	1		-	1.7	-	]
Gate resistance	R <sub>g</sub>	f = 1 MHz		3.1	6.05	9	Ω
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>			-	44	66	
Rise time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = -30 V, $R_L$ = 30 $\Omega$ $I_D \cong$ -1 A, $V_{GEN}$ = -4.5 V, $R_g$ = 1 $\Omega$		-	25	38	]
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>			-	13	20	ns -
Fall time <sup>c</sup>	t <sub>f</sub>			ı	9	14	
Source-Drain Diode Ratings and Char	acteristics <sup>b</sup>						
Pulsed current <sup>a</sup>	I <sub>SM</sub>			-	-	-6.7	Α
Forward voltage	$V_{SD}$	I <sub>F</sub> = ·	-0.5 A, V <sub>GS</sub> = 0 V	-	-0.8	-1.2	V

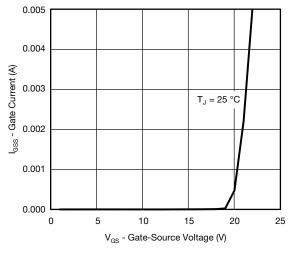
#### Notes

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

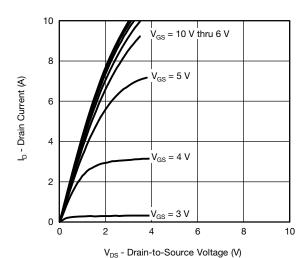
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



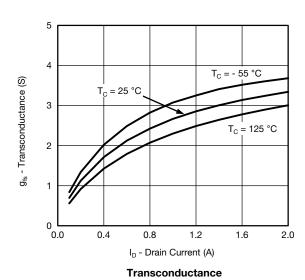
## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

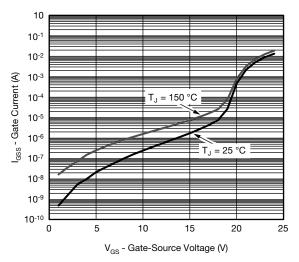


### Gate Current vs. Gate-Source Voltage

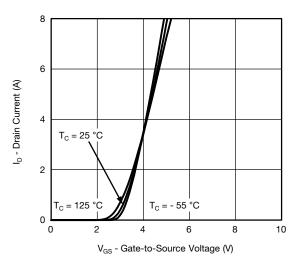


**Output Characteristics** 

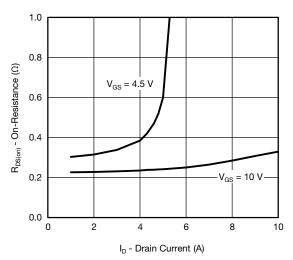




Gate Current vs. Gate-Source Voltage



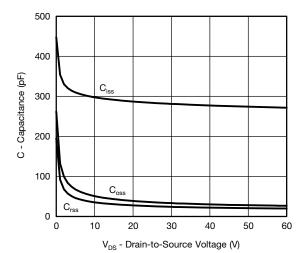
**Transfer Characteristics** 



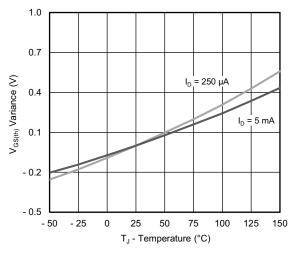
On-Resistance vs. Drain Current



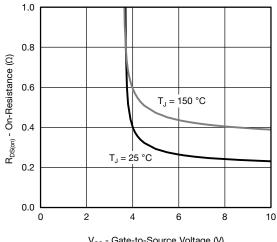
## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



#### Capacitance

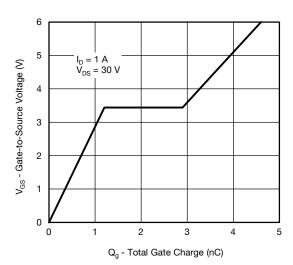


### **Threshold Voltage**

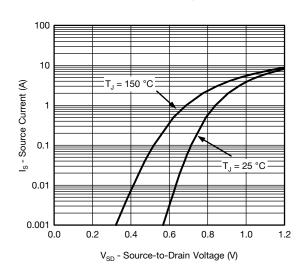


V<sub>GS</sub> - Gate-to-Source Voltage (V)

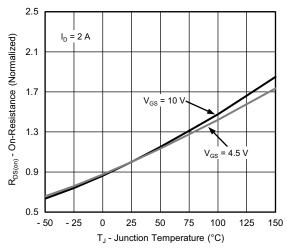
On-Resistance vs. Gate-to-Source Voltage



Gate Charge



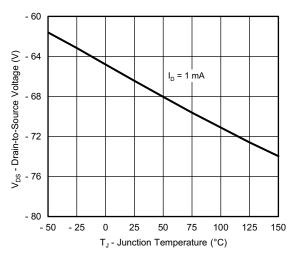
Source Drain Diode Forward Voltage



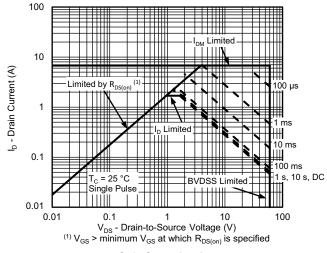
**On-Resistance vs. Junction Temperature** 



# TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



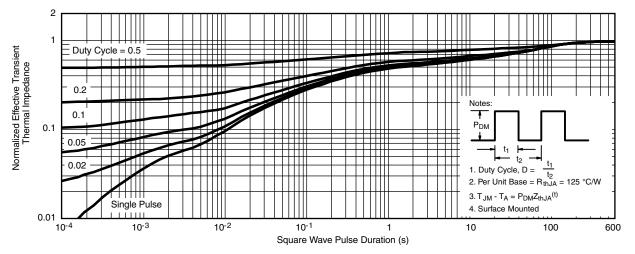
### Drain Source Breakdown vs. Junction Temperature



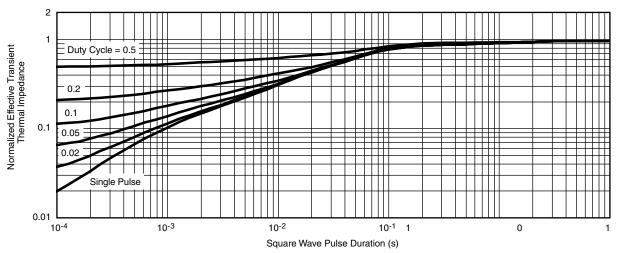
Safe Operating Area



# **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



### Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

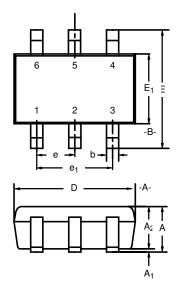
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

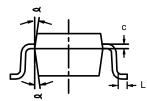
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### **SC-70: 6-LEADS**



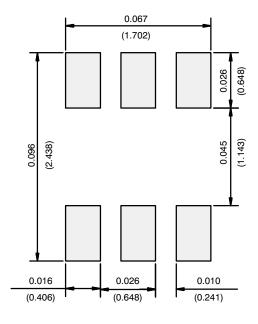


1	MILLIMETERS				S	
Dim	Min	Nom	Max	Min	Nom	Max
Α	0.90	_	1.10	0.035	_	0.043
<b>A</b> <sub>1</sub>	_	_	0.10	_	_	0.004
$A_2$	0.80	_	1.00	0.031	_	0.039
b	0.15	_	0.30	0.006	_	0.012
С	0.10	_	0.25	0.004	_	0.010
D	1.80	2.00	2.20	0.071	0.079	0.087
Е	1.80	2.10	2.40	0.071	0.083	0.094
E <sub>1</sub>	1.15	1.25	1.35	0.045	0.049	0.053
е	0.65BSC				0.026BSC	;
e <sub>1</sub>	1.20	1.30	1.40	0.047	0.051	0.055
L	0.10	0.20	0.30	0.004	0.008	0.012
۵	7°Nom				7°Nom	

DWG: 5550



### **RECOMMENDED MINIMUM PADS FOR SC-70: 6-Lead**



Recommended Minimum Pads Dimensions in Inches/(mm)

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